1 MEG UVEPROM
UV Erasable Programmable Read-Only Memory

AVAILABLE AS MILITARY SPECIFICATIONS
• SMD 5962-89614
• MIL-STD-883
• COTS-PEMS Version

FEATURES
• Organized 131,072 x 8
• Single +5V ±10% power supply
• Operationally compatible with existing megabit EPROMs
• Industry standard 32-pin ceramic dual-in-line package
• All inputs/outputs fully TTL compatible
• 8-bit output for use in microprocessor-based systems
• Very high-speed SNAP! Pulse Programming
• Power-saving CMOS technology
• 3-state output buffers
• 400mV minimum DC noise immunity with standard TTL loads
• Latchup immunity of 250 mA on all input and output pins
• No pullup resistors required
• Low power dissipation (Vcc = 5.5V)
  -Active - 165 mW Worst Case
  -Standby - 0.55 mW Worst Case (CMOS-input levels)

OPTIONS / MARKING
• **Timing**

120ns access	-12
150ns access	-15
200ns access	-20

• **Package(s)**

Ceramic DIP (600mils)	J	No. 114
Ceramic LCC (450 x 500mils)	ECA	No. 208

• **Operating Temperature Ranges**

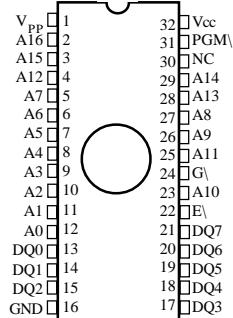|	
Military (-55°C to +125°C)	M
Industrial (-40°C to +85°C)	I

GENERAL DESCRIPTION

The SMJ27C010A series are 131072 by 8-bit (1048576-bit), ultaviolet (UV) light erasable, electrically programmable read-only memories (EPROMs).

These devices are fabricated using power-saving CMOS technology for high speed and simple interface with MOS and bipolar circuits. All inputs (including program data inputs) can be driven by Series 54 TTL circuits without the use of external pullup resistors. Each output can drive one Series 54 TTL circuit without external resistors.
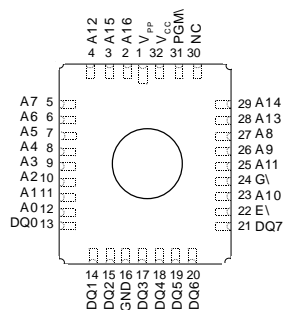
The SMJ27C010A EPROM is offered in a ceramic dual-in-line package (J suffix) designed for insertion in mounting-hole rows on 15.2mm (600mil) centers, and a 450 x 550 mil ceramic LCC package (ECA suffix).

PIN ASSIGNMENT
(Top View)

32-Pin DIP (J) (600 MIL)

V_PP	1	32	Vcc
A16	2	31	PGM\
A15	3	30	NC
A12	4	29	A14
A7	5	28	A13
A6	6	27	A8
A5	7	26	A9
A4	8	25	A11
A3	9	24	G\
A2	10	23	A10
A1	11	22	E\
A0	12	21	DQ7
DQ0	13	20	DQ6
DQ1	14	19	DQ5
DQ2	15	18	DQ4
GND	16	17	DQ3

32-Pin LCC (ECA) (450 x 550 mils)

Top: A12(4) A15(3) A16(2) V_PP(1) V_CC(32) PGM\(31) NC(30)

Left: A7 5, A6 6, A5 7, A4 8, A3 9, A2 10, A1 11, A0 12, DQ0 13

Right: 29 A14, 28 A13, 27 A8, 26 A9, 25 A11, 24 G\, 23 A10, 22 E\, 21 DQ7

Bottom: DQ1(14) DQ2(15) GND(16) DQ3(17) DQ4(18) DQ5(19) DQ6(20)

| Pin Name	Function
A0 - A18	Address Inputs
DQ0-DQ7	Inputs (programming)/Outputs
E\	Chip Enable
G\	Output Enable
GND	Ground
PGM\	Program
V_CC	5V Supply
V_PP	13V Power Supply*

Only in program mode.

These EPROMs operate from a single 5V supply (in the read mode), and therefore, are ideal for use in microprocessor-based systems. One other 13V supply is needed for programming. All programming signals are TTL level. These devices are programmable using the SNAP! Pulse programming algorithm. The SNAP! Pulse programming algorithm uses a V_PP of 13V and a V_CC of 6.5V for a nominal programming time of thirteen seconds. For programming outside the system, existing EPROM programmers can be used. Locations can be programmed singly, in blocks, or at random.

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FUNCTIONAL BLOCK DIAGRAM*
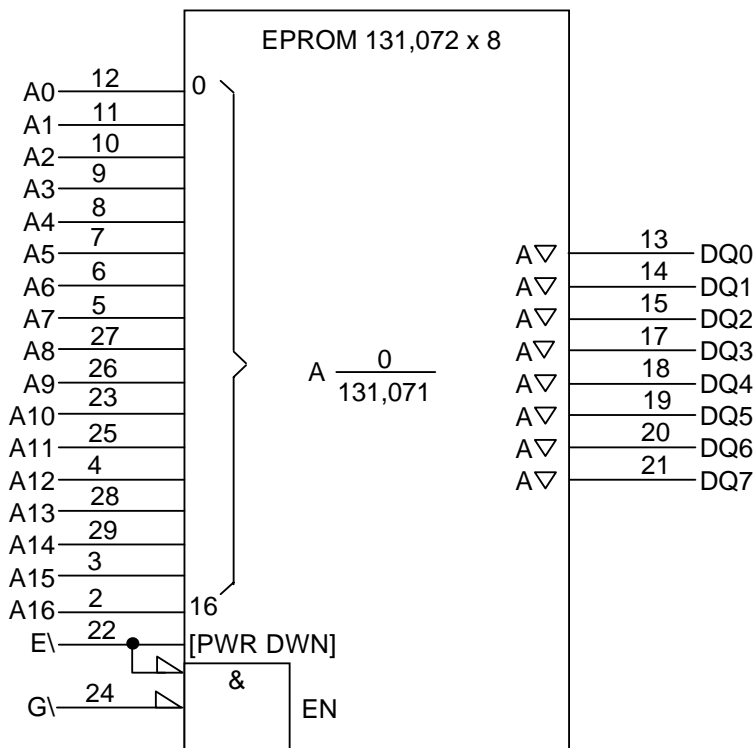
* This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. J package illustrated.

OPERATION

The seven modes of operation are listed in Table 1. The read mode requires a single 5V supply. All inputs are TTL level except for V_{PP} during programming (13V for SNAP! Pulse), and 12V on A9 for signature mode.

TABLE 1. OPERATION MODES

FUNCTION	MODE*							
	READ	OUTPUT DISABLE	STANDBY	PROGRAMMING	VERIFY	PROGRAM INHIBIT	SIGNATURE MODE	
E\	V_{IL}	V_{IL}	V_{IH}	V_{IL}	V_{IL}	V_{IH}	V_{IL}	
G\	V_{IL}	V_{IH}	X	V_{IH}	V_{IL}	X	V_{IL}	
PGM\	X	X	X	V_{IL}	V_{IH}	X	X	
V_{PP}	V_{CC}	V_{CC}	V_{CC}	V_{PP}	V_{PP}	V_{PP}	V_{CC}	
V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	
A9	X	X	X	X	X	X	V_{H}**	V_{H}**
A0	X	X	X	X	X	X	V_{IL}	V_{IH}
DQ0-DQ7	Data Out	High-Z	High-Z	Data In	Data Out	High-Z	CODE[#]	
							MFG	DEVICE
							97	D6

NOTES: * X can be V_{IL} or V_{IH}.
**V_{H} = 12V ± 0.5V
Die is Texas Instruments. User can program on benchtop programmer by selecting either TMS27C010A or SMJ27C010A from the device type selection menu.

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READ/OUTPUT DISABLE

When the outputs of two or more SMJ27C010As are connected in parallel on the same bus, the output of any particular device in the circuit can be read with no interference from competing outputs of the other devices. To read the output of a single device, a low level signal is applied to the E\ and G\ pins. All other devices in the circuit should have their outputs disabled by applying a high-level signal to one of these pins.

LATCHUP IMMUNITY

Latchup immunity on the SMJ27C010A is a minimum of 250mA on all inputs and outputs. This feature provides latchup immunity beyond any potential transients at the printed circuit board level when the devices are interfaced to industry-standard TTL or MOS logic devices. The input/output layout approach controls latchup without compromising performance or packing density.

POWER DOWN

Active I_{CC} supply current can be reduced from 30mA to 500µA by applying a high TTL input on E\ and to 100µA by applying a high CMOS input on E\. In this mode all outputs are in the high-impedance state.

ERASURE

Before programming, the SMJ27C010A EPROM is erased by exposing the chip through the transparent lid to a high-intensity ultraviolet light (wavelength 2537 Å). The recommended minimum exposure dose (UV intensity x exposure time) is 15-W·s/cm². A typical 12-mW/cm², filterless UV lamp erases the device in 21 minutes. The lamp should be located about 2.5cm above the chip during erasure. After erasure, all bits are in the high state. It should be noted that normal ambient light contains the correct wavelength for erasure; therefore, when using the SMJ27C010A, the window should be covered with an opaque label. After erasure (all bits in logic high state), logic lows are programmed into the desired locations. A programmed low can be erased only by ultraviolet light.

SNAP! PULSE PROGRAMMING

The SMJ27C010A is programmed by using the SNAP! Pulse programming algorithm as illustrated by the flow chart (Figure 1). This algorithm programs in a nominal time of thirteen seconds. Actual programming time varies as a function of the programmer used.

The SNAP! Pulse programming algorithm uses an initial pulse of 100 microseconds (µs) followed by a byte verification to determine when the addressed byte has been successfully programmed. Up to ten 100µs pulses per byte are provided before a failure is recognized.

The programming mode is achieved when V_{PP} = 13V, V_{CC}= 6.5V, E\ = V_{IL}, and G\ = V_{IH}. Data is presented in parallel (eight bits) on pins DQ0 through DQ7. Once addresses and data are stable, PGM\ is pulsed low.

More than one device can be programmed when the devices are connected in parallel. Locations can be programmed in any order. When the SNAP! Pulse programming routine is complete, all bits are verified with V_{CC} = V_{PP} = 5V ± 10%.

PROGRAM INHIBIT

Programming can be inhibited by maintaining high level inputs on the E\ or the PGM\ pins.

PROGRAM VERIFY

Programmed bits can be verified with V_{PP} = 13V when G\ = V_{IL}, and E\ = V_{IL}, and PGM\ = V_{IH}.

SIGNATURE MODE

The signature mode provides access to a binary code identifying the manufacturer and type. This mode is activated when A9 (pin 26) is forced to 12V. Two identifier bytes are accessed by toggling A0. All other addresses must be held low. The signature code for these devices is 97D6. A0 low selects the manufacturer's code 97 (Hex), and A0 high selects the device code D6 (Hex), as shown in Table 2.

TABLE 2. SIGNATURE MODES

IDENTIFIER*	PINS									
	A0	DQ7	DQ6	DQ5	DQ4	DQ3	DQ2	DQ1	DQ0	HEX
MANUFACTURER CODE	V_{IL}	1	0	0	1	0	1	1	1	97
DEVICE CODE	V_{IH}	1	1	0	1	0	1	1	0	D6

* E\ = G\ = V_{IL}, A1 - A8 = V_{IL}, A9 = V_H, A10 - A16 = V_{IL}, V_{PP} = V_{CC}.

FIGURE 1. SNAP! PULSE PROGRAMMING FLOW CHART

START

Address = First Location

V_{CC} = 6.5V ± 0.25V, V_{PP} = 13V ± 0.25V

Program One Pulse = t_W = 100µs ← Increment Address

Program Mode

Last Address? — No

Yes

Address = First Location

X = 0 ← Increment Address

Program One Pulse = t_W = 100µs

Verify One Byte — Fail → X = X+1 → X = 10? — No

Interactive Mode

Pass

Last Address? — No → Increment Address

Yes

V_{CC} = V_{PP} = 5V ± 0.5V

X = 10? — Yes → Device Failed

Compare All Bytes to Original Data — Fail → Device Failed

Final Verification

Pass

Device Passed

ABSOLUTE MAXIMUM RATINGS*

Supply Voltage Range, V_{CC}**............................-0.6V to +7.0V

Supply Voltage Range, V_{pp}**.........................-0.6V to +14.0V

Input Voltage Range, All inputs except A9**..-0.6V to V_{CC}+1

A9.....-0.6V to +13.5V

Output Voltage Range,

with respect to V_{SS}**..................................-0.6V to V_{CC} +1

Operating Free-air Temperature Range, T_A....-55°C to 125°C

Storage Temperature Range, T_{stg}.....................-65°C to 150°C

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

** All voltage values are with respect to GND.

RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V_{CC}	Supply Voltage	Read Mode[1]	4.5	5	5.5	V
		SNAP! Pulse programming algorithm	6.25	6.5	6.75	V
V_{PP}	Supply Voltage	Read Mode[2]	V_{CC}-0.6	V_{CC}	V_{CC}+0.6	V
		SNAP! Pulse programming algorithm	12.75	13	13.25	V
V_{IH}	High-level DC input voltage	TTL	2		V_{CC}+0.5	V
		CMOS	V_{CC}-0.2		V_{CC}+0.5	V
V_{IL}	Low-level DC input voltage	TTL	-0.5		0.8	V
		CMOS	-0.5		GND+0.2	V
T_A	Operating free-air temperature		-55		125	°C

NOTES:

1. V_{CC} must be applied before or at the same time as V_{PP} and removed after or at the same time as V_{PP}. The deivce must not be inserted into or removed from the board when V_{PP} or V_{CC} is applied.

2. During programming, V_{PP} must be maintained at $13V \pm 0.25V$.

ELECTRICAL CHARACTERISTICS OVER RECOMMENDED RANGES OF SUPPLY VOLTAGE AND OPERATING FREE-AIR TEMPERATURE

PARAMETER			TEST CONDITIONS	MIN	MAX	UNIT
V_{OH}	High-level DC output voltage		I_{OH} = -20µA	V_{CC}-0.2		V
			I_{OH} = -2.5mA	3.5		
V_{OL}	Low-level DC output voltage		I_{OL} = 2.1mA		0.4	V
			I_{OL} = 20µA		0.1	
I_I	Input current (leakage)		V_I = 0V to 5.5V		±1	µA
I_O	Output current (leakage)		V_O = 0V to V_{CC}		±1	µA
I_{PP1}	V_{PP} supply current		V_{PP} = V_{CC} = 5.5V		10	µA
I_{PP2}	V_{PP} supply current (during program pulse)		V_{PP} = 13V		50	mA
I_{CC1}	V_{CC} supply current (standby)	TTL-Input Level	V_{CC} = 5.5V, E\=V_{IH}		500	µA
		CMOS-Input Level	V_{CC} = 5.5V, E\=V_{CC}±0.2V		100	
I_{CC2}	V_{CC} supply current (active) (output open)		E\=V_{IL}, V_{CC}=5.5V t_{cycle} = minimum cycle time, outputs open[1]		30	mA

NOTES:

1. Minimum cycle time = maximum access time.

CAPACITANCE OVER RECOMMENDED RANGES OF SUPPLY VOLTAGE AND OPERATING FREE-AIR TEMPERATURE, f = 1MHz*

	PARAMETER	TEST CONDITIONS	TYP**	MAX	UNIT
C_I	Input capacitance	V_I = 0V, f = 1MHz	4	8	pF
C_O	Output capacitance	V_O = 0V, f= 1 MHz	6	10	pF

* Capacitance measurements are made on sample basis only.

** All typical values are at T_A = 25°C and nominal voltages.

SWITCHING CHARACTERISTICS OVER RECOMMENDED RANGES OF OPERATING CONDITIONS[1,2]

	PARAMETER	TEST CONDITIONS	-12		-15		-20		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
$t_{a(A)}$	Access time from address	C_L = 100pF 1 Series 74 TTL Load, Input t_r < 20ns, Input t_f < 20ns		120		150		200	ns
$t_{a(E)}$	Access time from chip enable			120		150		200	ns
$t_{en(G)}$	Output enable time from G\			55		75		75	ns
t_{dis}	Output disable time from G\ or E\, whichever occurs first[3]		0	50	0	60	0	60	ns
$t_{v(A)}$	Output data valid time after change of address, E\, or G\, whichever occurs first[3]		0		0		0		ns

NOTES:

1. For all switching characteristics, the input pulse levels are 0.4V to 2.4V. Timing measurements are made at 2V for logic high and 0.8V for logic low. (Reference AC testing waveform)

2. Common test conditions apply for t_{dis} except during programming.

3. Value calculated from 0.5V delta to measured output level.

SWITCHING CHARACTERISTICS FOR PROGRAMMING: V_{CC} = 6.5V and V_{PP} = 13V (SNAP! Pulse), T_A = 25°C[1]

|	PARAMETER	MIN	MAX	UNIT
$t_{dis(G)}$	Disable, Output disable time from G\	0	130	ns
$t_{en(G)}$	Enable, Output enable time from G\		150	ns

NOTE: 1. For all switching characteristics, the input pulse levels are 0.4V to 2.4V. Timing measurements are made at 2V for logic high and 0.8V for logic low (reference AC testing waveform).

TIMING REQUIREMENTS FOR PROGRAMMING

			MIN	TYP	MAX	UNIT
$t_{w(PGM)}$	Pulse duration, program	SNAP! Pulse Programming Algorithm	95	100	105	µs
$t_{su(A)}$	Setup Time, Address		2			µs
$t_{su(E)}$	Setup Time, E\		2			µs
$t_{su(G)}$	Setup Time, G\		2			µs
$t_{su(D)}$	Setup Time, Data		2			µs
$t_{su(Vpp)}$	Setup Time, V_{PP}		2			µs
$t_{su(Vcc)}$	Setup Time, V_{CC}		2			µs
$t_{h(A)}$	Hold time, address		0			µs
$t_{h(D)}$	Hold time, data		2			µs

PARAMETER MEASUREMENT INFORMATION

2.08V

$R_L = 800\Omega$

Output Under Test

$C_L = 100\ pF^1$
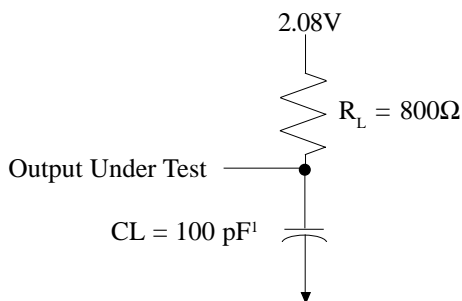
NOTES:
1. C_L includes probe and fixture capacitance.

FIGURE 2. AC TEST OUTPUT LOAD CIRCUIT WAVEFORM

2.4 V

0.4 V

2 V

0.8 V

2 V

0.8 V
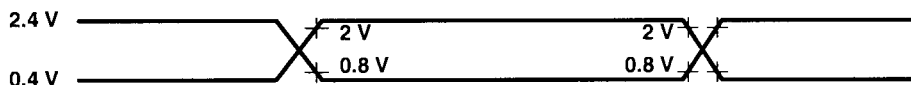
AC testing inputs are driven at 2.4V for logic high and 0.4V for logic low. Timing measurements are made at 2V for logic high and 0.8V for logic low for both inputs and outputs.

FIGURE 3. READ-CYCLE TIMING

SMJ27C010A
AS27C010A
Rev. 3.5 10/03

7

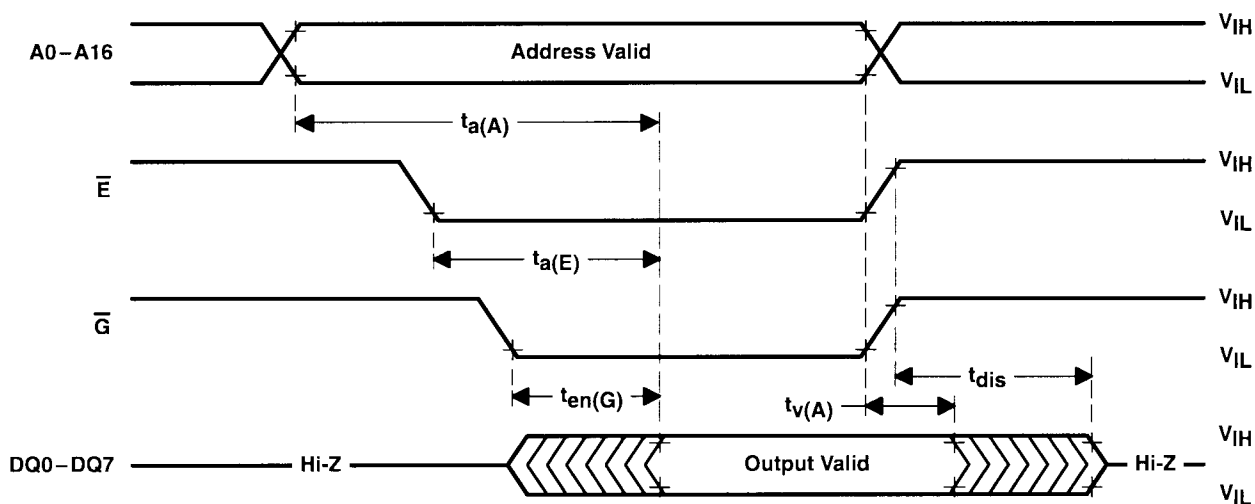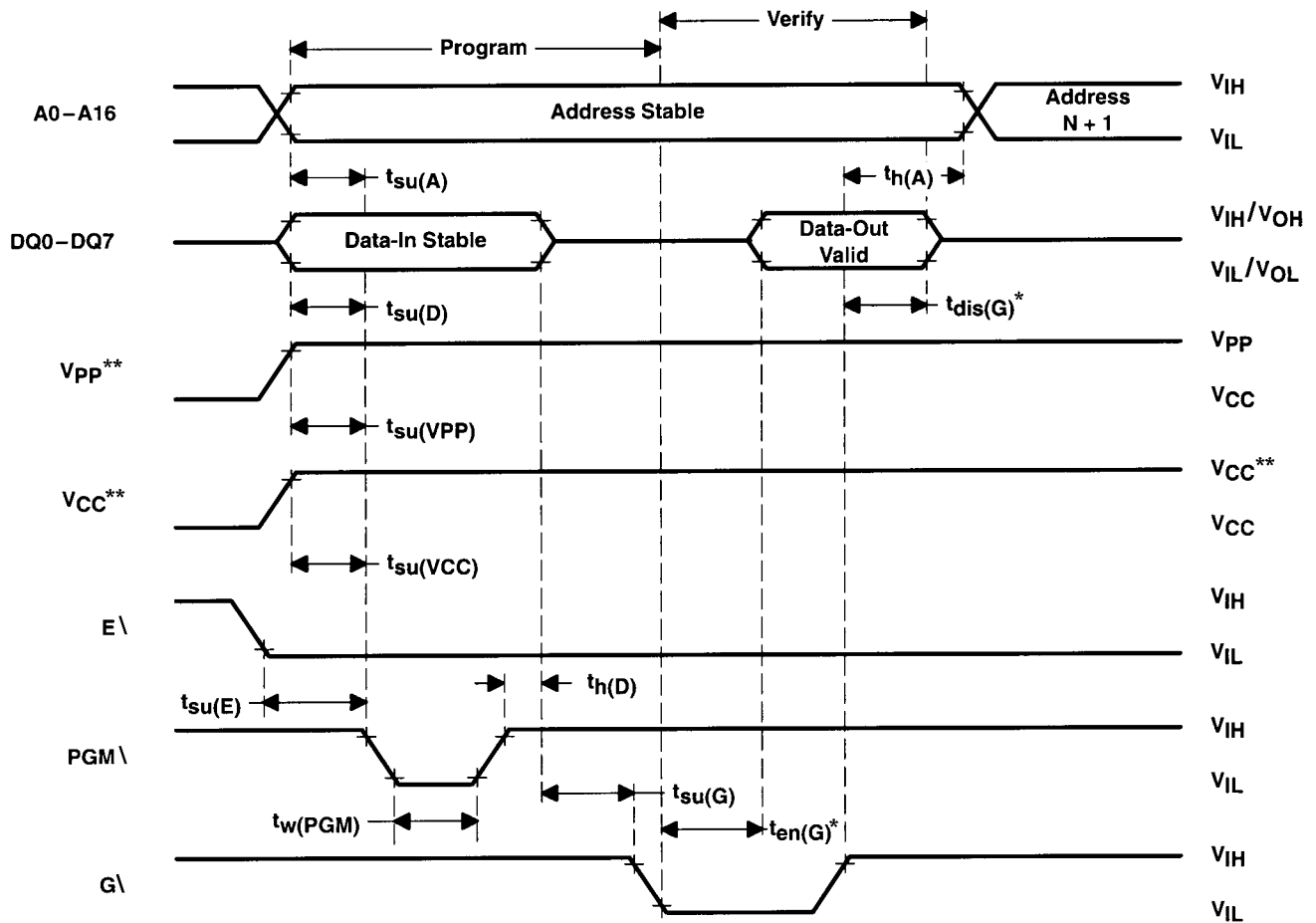Austin Semiconductor, Inc. reserves the right to change products or specifications without notice.

FIGURE 4. PROGRAM-CYCLE TIMING (SNAP! PULSE PROGRAMMING)

* $t_{dis(G)}$ and $t_{en(G)}$ are characteristics of the device but must be accommodated by the programmer.
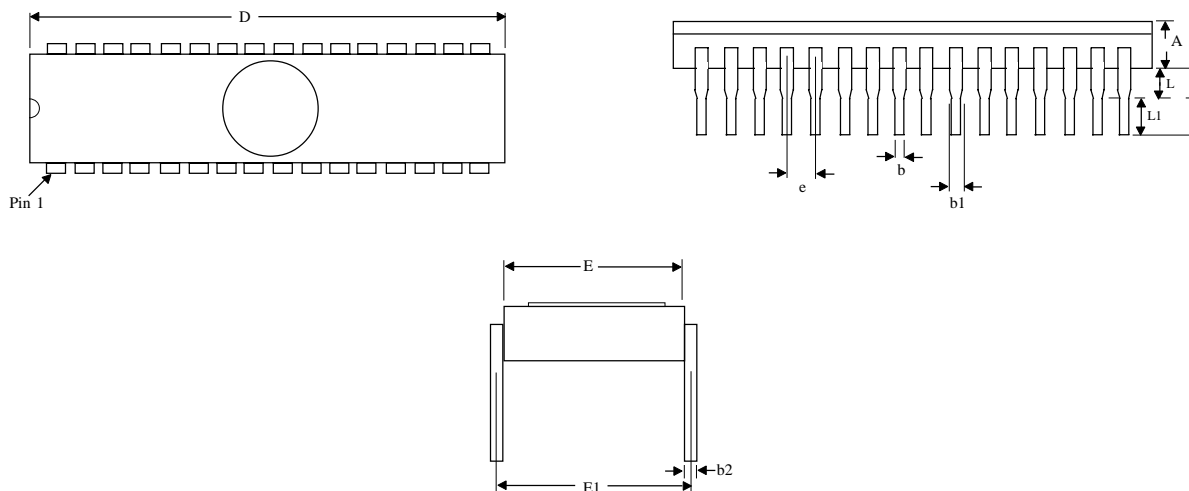** 13V V_{PP} and 6.5V V_{CC} for SNAP! Pulse programming.

SMJ27C010A
AS27C010A
Rev. 3.5 10/03

8

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MECHANICAL DEFINITION*

ASI Case #114 (Package Designator J)
SMD 5962-89614, Case Outline X

	SMD Specifications	
SYMBOL	**MIN**	**MAX**
A	---	0.225
b	0.014	0.026
b1	0.045	0.065
b2	0.008	0.018
D	---	1.680
E	0.510	0.620
e	0.100 BSC	
E1	0.600 BSC	
L1	0.125	0.200
L	0.015	0.070

NOTE: *These dimensions are per the SMD. ASI's package dimensional limits may differ, but they will be within the SMD limits.*

All measurements are in inches.

MECHANICAL DEFINITIONS*

ASI Case #208 (Package Designator ECA)
SMD 5962-89614, Case Outline Y

Detail A

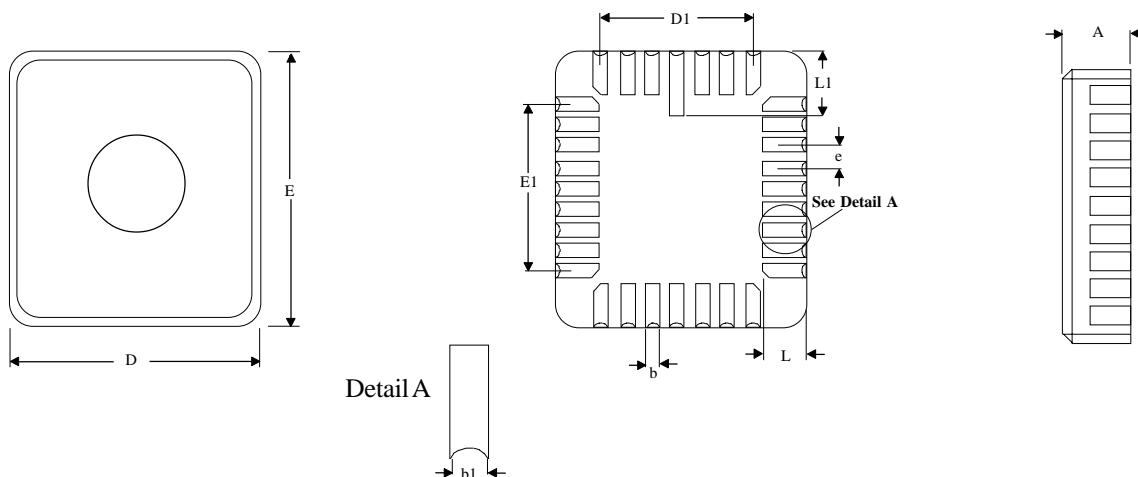|	SMD SPECIFICATIONS	
SYMBOL	MIN	MAX
A	0.060	0.120
b	0.022	0.028
b1	0.006	0.022
D	0.442	0.458
D1	0.300 BSC	
E	0.540	0.560
E1	0.400 BSC	
e	0.050 BSC	
L	0.045	0.055
L1	0.075	0.095

NOTE: *These dimensions are per the SMD. ASI's package dimensional limits may differ, but they will be within the SMD limits.*

All measurements are in inches.

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ORDERING INFORMATION

EXAMPLE: SMJ27C010A-12JM

Device Number	Speed ns	Package Type	Operating Temperature	Available Processes
SMJ27C010A	-12	J	*	+
SMJ27C010A	-15	J	*	+
SMJ27C010A	-20	J	*	+

EXAMPLE: AS27C010A-15ECAM/Q

Device Number	Speed ns	Package Type	Operating Temperature	Available Processes
AS27C010A	-12	ECA	*	#
AS27C010A	-15	ECA	*	#
AS27C010A	-20	ECA	*	#

NOTES:
+ SMJ prefix, MIL-STD-883C processing
SM prefix, commercial processing
AS prefix, commercial or MIL-STD-883C processing
(see note #)

*OPERATING TEMPERATURE
M = Extended Temperature Range   -55°C to +125°C
I = Industrial Temperature Range   -40°C to +85°C

AVAILABLE PROCESSES
/Q   = For "AS" prefix part numbers only, indicates that part is processed to MIL-STD-883C.

Blank = For SMJ prefix part numbers, the /Q suffix is not used, as the SMJ prefix indicates MIL-STD-883C processing. Also blank for AS prefix part numbers indicating commercially (non MIL-STD-883C) processed parts.

SMJ27C010A
AS27C010A
Rev. 3.5 10/03

11

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ASI TO DSCC PART NUMBER
CROSS REFERENCE*

ASI Package Designator ECA

TI Part #**	SMD Part #
AS27C010A-12ECAM/Q	5962-8961420QYA
AS27C010A-15ECAM/Q	5962-8961419QYA
AS27C010A-20ECAM/Q	5962-8961417QYA

ASI Package Designator J

TI Part #**	SMD Part #
SMJ27C010A-12JM	5962-8961420QXA
SMJ27C010A-15JM	5962-8961419QXA
SMJ27C010A-20JM	5962-8961417QXA

ASI part number is for reference only. Orders received referencing the SMD part number will be processed per the SMD.
**Parts are listed on SMD under the old Texas Instruments part number. ASI purchased this product line in November of 1999.*

SMJ27C010A
AS27C010A
Rev. 3.5 10/03

12

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